

СПИСК
НА ЗАБЕЛЯЗАНИТЕ НЕЗАВИСИМИ ЦИТИРАНИЯ

на гл. асистент д-р Ирина Бинева
Общ брой – 168

- I. **D. Nesheva, C. Raptis, A. Perakis, I. Bineva, Z. Aneva, Z. Levi, S. Alexandrova, H. Hofmeister, “Raman scattering and photoluminescence from Si nanoparticles in annealed SiO_x thin films”, *J. Appl. Phys.*, **92** (2002) 4678-83.**
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